

December 2014

# MOCD207M, MOCD208M, MOCD211M, MOCD213M, MOCD217M 8-pin SOIC Dual-Channel Phototransistor Output Optocoupler

#### **Features**

- Closely Matched Current Transfer Ratios
- Minimum BV<sub>CEO</sub> of 70 V Guaranteed
- MOCD207M, MOCD208M
- Minimum BV<sub>CEO</sub> of 30 V Guaranteed
  - MOCD211M, MOCD213M, MOCD217M
- Low LED Input Current Required for Easier Logic Interfacing
  - MOCD217M
- Convenient Plastic SOIC-8 Surface Mountable Package Style, with 0.050" Lead Spacing
- Safety and Regulatory Approvals:
  - UL1577, 2,500 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

## **Applications**

- Feedback Control Circuits
- Interfacing and Coupling Systems of Different Potentials and Impedances
- General Purpose Switching Circuits
- Monitor and Detection Circuits

## **Description**

These devices consist of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline, plastic package. They are ideally suited for high-density applications, and eliminate the need for through-the-board mounting.

#### **Schematic**

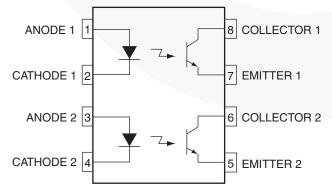


Figure 1. Schematic

#### **Package Outline**

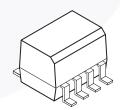


Figure 2. Package Outline

# **Safety and Insulation Ratings**

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–III
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	565	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	4000	V <sub>peak</sub>
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T <sub>S</sub>	Case Temperature <sup>(1)</sup>	150	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	200	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	300	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V <sup>(1)</sup>	> 109	Ω

#### Note:

1. Safety limit values – maximum values allowed in the event of a failure.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Rating	Value	Unit
TOTAL DEVI	CE		
T <sub>STG</sub>	Storage Temperature	-40 to +125	°C
T <sub>A</sub>	Ambient Operating Temperature	-40 to +100	°C
T <sub>J</sub>	Junction Temperature	-40 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C
	Total Device Power Dissipation @ T <sub>A</sub> = 25°C	240	mW
$P_{D}$	Derate Above 25°C	2.94	mW/°C
EMITTER			
I <sub>F</sub>	Continuous Forward Current	60	mA
I <sub>F</sub> (pk)	Forward Current – Peak (PW = 100 µs, 120 pps)	1.0	Α
V <sub>R</sub>	Reverse Voltage	6.0	V
$P_{D}$	LED Power Dissipation @ T <sub>A</sub> = 25°C	90	mW
	Derate Above 25°C	0.8	mW/°C
DETECTOR			
I <sub>C</sub>	Continuous Collector Current	150	mA
	Collector-Emitter Voltage		
$V_{CEO}$	MOCD207M, MOCD208M, MOCD213M	70	V
	MOCD211M, MOCD217M	30	V
V <sub>ECO</sub>	Emitter-Collector Voltage	7	V
В	Detector Power Dissipation @ T <sub>A</sub> = 25°C	150	mW
$P_{D}$	Derate Above 25°C	1.76	mW/°C

## **Electrical Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER				1		
	Input Forward Voltage					
	MOCD217M	I <sub>F</sub> = 1 mA		1.05	1.3	V
$V_{F}$	MOCD213M	I <sub>F</sub> = 10 mA		1.15	1.5	V
	MOCD207M, MOCD208M, MOCD211M	I <sub>F</sub> = 30 mA		1.25	1.5	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6 V		0.001	100	μΑ
C <sub>IN</sub>	Input Capacitance			18		pF
DETECTO	OR .					
	Callantay Fraittay Dayly Courset	$V_{CE} = 10 \text{ V}, T_{A} = 25^{\circ}\text{C}$		1.0	50	nA
I <sub>CEO</sub>	Collector-Emitter Dark Current	V <sub>CE</sub> = 10 V, T <sub>A</sub> = 100°C		1.0		μA
	Collector-Emitter Breakdown Voltage					
BV <sub>CEO</sub>	MOCD211M, MOCD217M	$I_{C} = 100 \ \mu A$	30	100		V
D V CEO	MOCD207M, MOCD208M, MOCD213M	I <sub>C</sub> = 100 μA	70	100		V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 100 μA	7	10		V
C <sub>CE</sub>	Collector-Emitter Capacitance	f = 1.0 MHz, V <sub>CE</sub> = 0		7		pF
COUPLE	D		•	•		
	Collector-Output Current					
	MOCD207M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	100		200	%
CTD	MOCD208M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	40		125	%
CTR	MOCD211M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	20			%
	MOCD213M	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	100			%
	MOCD217M	I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 5 V	100			%
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 mA, I <sub>F</sub> = 10 mA			0.4	V
t <sub>on</sub>	Turn-On Time	$I_C = 2$ mA, $V_{CC} = 10$ V, $R_L = 100 \Omega$ (Figure 8)		7.5		μs
t <sub>off</sub>	Turn-Off Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		5.7		μs
t <sub>r</sub>	Rise Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		3.2		μs
t <sub>f</sub>	Fall Time	$I_{C} = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_{L} = 100 \Omega \text{ (Figure 8)}$		4.7		μs

## **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Input-Output Isolation Voltage	t = 1 Minute	2500			VAC <sub>RMS</sub>
C <sub>ISO</sub>	Isolation Capacitance	V <sub>I-O</sub> = 0 V, f = 1 MHz		0.2		pF
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = ±500 VDC, T <sub>A</sub> = 25°C	10 <sup>11</sup>			Ω

# **Typical Performance Curves**

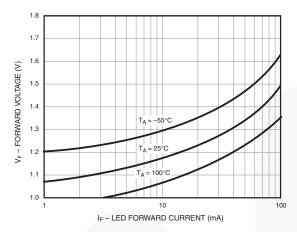


Figure 3. LED Forward Voltage vs. Forward Current

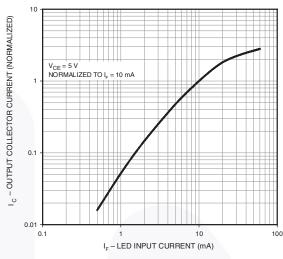


Figure 4. Output Curent vs. Input Current

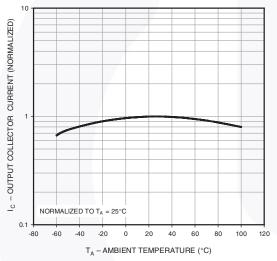


Figure 5. Output Current vs. Ambient Temperature

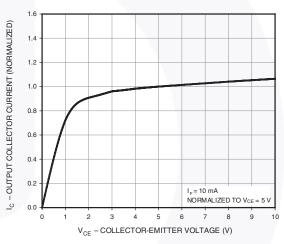


Figure 6. Output Current vs. Collector-Emitter Voltage

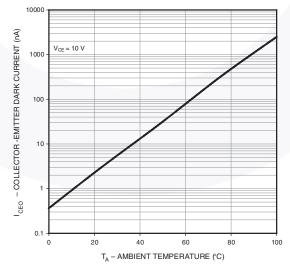


Figure 7. Dark Current vs. Ambient Temperature

# **Switching Time Test Circuit and Waveforms**

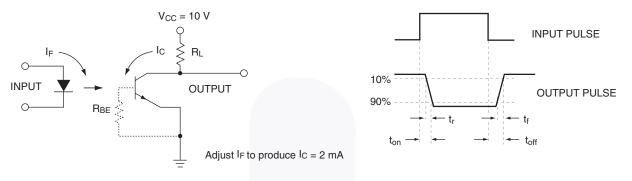


Figure 8. Switching Time Test Circuit and Waveforms

## **Reflow Profile**

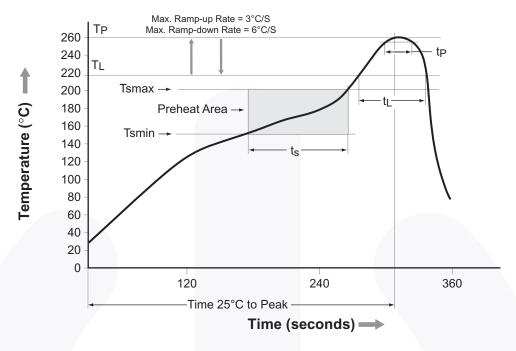


Figure 9. Reflow Profile

Profile Freature	Pb-Free Assembly Profile	
Temperature Minimum (Tsmin)	150°C	
Temperature Maximum (Tsmax)	200°C	
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second maximum	
Liquidous Temperature (T <sub>L</sub> )	217°C	
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60-150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second maximum	
Time 25°C to Peak Temperature	8 minutes maximum	

# **Ordering Information**

Part Number	Package	Packing Method	
MOCD207M	Small Outline 8-Pin	Tube (100 Units)	
MOCD207R2M	Small Outline 8-Pin	Tape and Reel (1000 Units)	
MOCD207VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)	
MOCD207R2VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)	

#### Note:

2. The product orderable part number system listed in this table also applies to the MOCD208M, MOCD211M, MOCD213M, and MOCD217M products.

# **Marking Information**

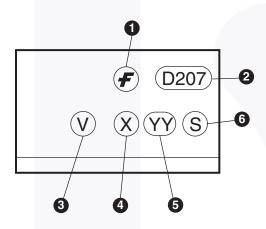
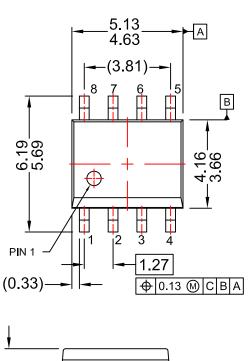
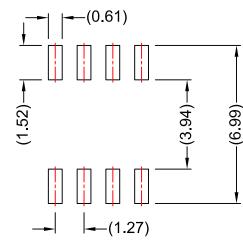


Figure 10. Top MarkTop Mark

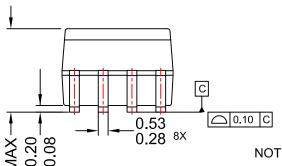
#### **Table 1. Top Mark Definitions**

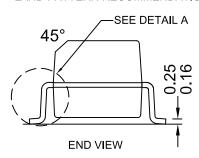
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code





LAND PATTERN RECOMMENDATION



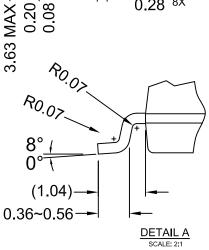






- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M.
- E) DRAWING FILENAME: MKT-M08Erev5









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